

Title (en)  
SUBSTRATE OF THE SEMI-CONDUCTOR-ON-INSULATOR TYPE FOR RADIOFREQUENCY APPLICATIONS

Title (de)  
SUBSTRAT VOM HALBLEITER-AUF-ISOLATORTYP FÜR HOCHFREQUENZANWENDUNGEN

Title (fr)  
SUBSTRAT DE TYPE SEMI-CONDUCTEUR SUR ISOLANT POUR DES APPLICATIONS RADIOFRÉQUENCES

Publication  
**EP 3900029 A1 20211027 (FR)**

Application  
**EP 19848883 A 20191219**

Priority  
• FR 1873888 A 20181221  
• FR 2019053192 W 20191219

Abstract (en)  
[origin: WO2020128354A1] The present invention relates to a substrate (1) of the semi-conductor-on-insulator type for radiofrequency applications, comprising: - a carrier substrate (2) of silicon, - an electrically insulating layer (3) which is arranged on the carrier substrate, - a monocrystalline layer (4) which is arranged on the electrically insulating layer, the substrate (1) mainly being characterised in that it further comprises a layer of silicon carbide SiC (5) which is arranged between the carrier substrate (2) and the electrically insulating layer (3), which has a thickness between 1 nm and 5 nm, the surface (6) of the layer of silicon carbide SiC which is at the side of the electrically insulating layer (3) being rough.

IPC 8 full level  
**H01L 21/762** (2006.01); **H01L 21/20** (2006.01); **H01L 21/322** (2006.01)

CPC (source: EP KR US)  
**H01L 21/02002** (2013.01 - EP KR US); **H01L 21/3226** (2013.01 - EP KR US); **H01L 21/76254** (2013.01 - EP KR US);  
**H01L 27/1207** (2013.01 - US)

Designated contracting state (EPC)  
AL AT BE BG CH CY CZ DE DK EE ES FI FR GB GR HR HU IE IS IT LI LT LU LV MC MK MT NL NO PL PT RO RS SE SI SK SM TR

Designated extension state (EPC)  
BA ME

DOCDB simple family (publication)  
**WO 2020128354 A1 20200625**; CN 113196461 A 20210730; EP 3900029 A1 20211027; FR 3091011 A1 20200626; FR 3091011 B1 20220805; JP 2022510822 A 20220128; JP 7342330 B2 20230912; KR 20210105403 A 20210826; SG 11202105731R A 20210729; US 2022076991 A1 20220310

DOCDB simple family (application)  
**FR 2019053192 W 20191219**; CN 201980082744 A 20191219; EP 19848883 A 20191219; FR 1873888 A 20181221; JP 2021528376 A 20191219; KR 20217022738 A 20191219; SG 11202105731R A 20191219; US 201917416948 A 20191219